



Shi-Xi Kong

Ph.D. Student in Electrical Engineering, admitted Autumn 2026

 Curriculum Vitae available Online

Bio

BIO

Shi-Xi Kong is an incoming EE PhD student at Stanford. His research interest lies in translating scientific insights into practical device technologies for logic, memory, and emerging computing paradigms.

Over the past three years, as a undergraduate research assistant at NYCU, he worked on emerging memory devices such as FTJ and STT-MRAM, focusing on their device physics and applications.

He is now studying trap-assisted tunneling and quantum transport at 2D contacts.

HONORS AND AWARDS

- Stanford Graduate Fellowship, Stanford University (2026 – 2029)
- TSMC-NYCU Research Assistantship, TSMC-NYCU Joint Research Center (2023 – 2024)

LINKS

- Google Scholar: https://scholar.google.com/citations?hl=zh-TW&user=_iQCWI8AAAAJ&view_op=list_works&sortby=pubdate
- LinkedIn: <https://www.linkedin.com/in/shi-xi-kong/>

Publications

PUBLICATIONS

- **Theoretical investigation of performance-improved ferroelectric tunnel junction based on trap-assisted tunneling** *APPLIED PHYSICS LETTERS*
Kong, S., Hou, T.
2025; 127 (26)